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(71) Applicant (for all designated States except US): CUBIC WAFER, INC. [US/US]; 10 Al Paul Lane, Merrimack, New Hampshire 03054 (US).

(72) Inventor; and

(75) Inventor/Applicant (for US only): TREZZA, John [US/US]; 12 White Oak Drive, Nashua, New Hampshire 03063 (US).

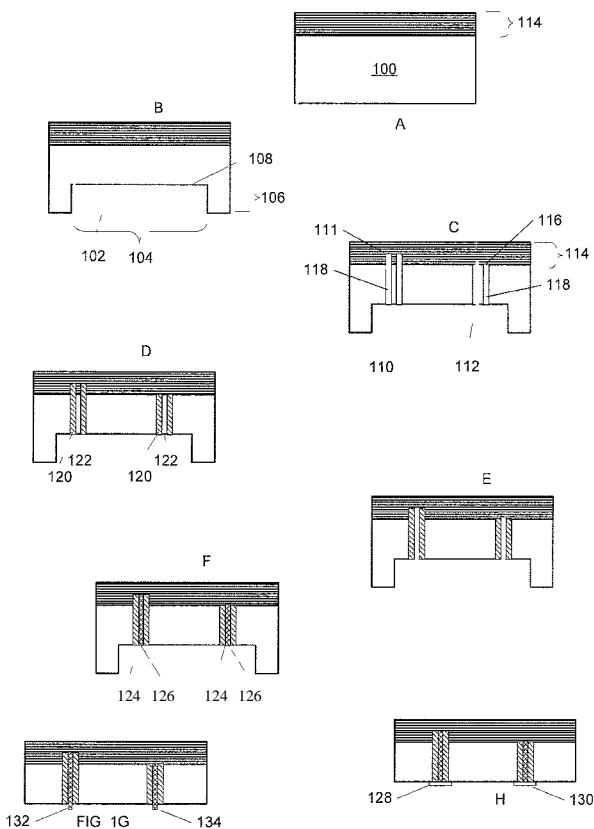
(74) Agent: STRAUSSMAN, Richard; Morgan & Finnegan LLP, Three World Financial Center, New York, New York 10281-2101 (US).

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[Continued on next page]

(54) Title: WAFER VIA FORMATION



(57) Abstract: A method of electrically conductive via formation in a fully processed wafer involves defining at least one trench area on a backside of the fully processed wafer, forming at least one trench within the trench area to an overall depth that will allow for a via formed within the trench to be seeded over its full length, forming the via within the trench into the fully processed wafer to a predetermined depth, depositing a seed layer over the full length of the via, and plating the seed layer to fill the via with an electrically conductive metal.

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USPC - 257/98

According to International Patent Classification (IPC) or to both national classification and IPC

B FIELDS SEARCHED

Minimum documentation searched (classification system followed by classification symbols)
USPC - 257/98Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched
USPC - 257/98,750,E21 211, \$, 438/26, \$
Search Terms BelowElectronic data base consulted during the international search (name of data base and, where practicable, search terms used)
PubWEST (USPT, PGPB, EPAB, JPAB), google com

Search Terms Used via, formation, trench backside, seed, wet, dry, chip, trench area, sawing, dicing, periphery, peripheral, aligned

C DOCUMENTS CONSIDERED TO BE RELEVANT

Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No
X	US 6,790,775 B2 (Fartash) 14 September 2004 (14 09 2004), entire document, especially Abstract, col 1, ln 45-46, col 3, ln 45-47, col 6, ln 50-55, col 7, ln 11-31	1-4, 8-12, 15, 19, 20
Y		----- 5-7, 13, 14, 16-18
Y	US 5,075,253 A (Slawa, Jr) 24 December 1991 (24 12 1991), entire document, especially Abstract, col 25, ln 60-62	7
Y	US 6,498,387 B1 (Yang) 24 December 2002 (24 12 2002), entire document, especially Abstract, col 2, ln 48-50	13, 14, 17, 18
Y	US 6,887,792 B2 (Perlov et al) 03 May 2005 (03 05 2005), entire document, especially Abstract, col 4, ln 3-7, FIG 4	5, 6
Y	US 6,013,551 A (Chen et al) 11 January 2000 (11 01 2000), entire document, especially Abstract, col 6, ln 48-52	16

D Further documents are listed in the continuation of Box C

* Special categories of cited documents		
"A" document defining the general state of the art which is not considered to be of particular relevance	"T"	later document published after the international filing date or priority date and not in conflict with the application but cited to understand the principle or theory underlying the invention
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"O" document referring to an oral disclosure, use, exhibition or other means	"&"	document member of the same patent family
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Name and mailing address of the ISA/US
Mail Stop PCT, Attn ISA/US, Commissioner for Patents
P O Box 1450, Alexandria, Virginia 22313-1450
Facsimile No 571-273-3201

Authorized officer

Lee W Young

PCT Helpdesk 571 272-4300
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